

SILICON NPN PHOTO DETECTOR

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DESCRIPTION:

The **2N5777(MOD.)** is Designed for General Purpose Industrial Photo Detector Applications.

FEATURES:

- High Sensitivity
- Economical TO-92 compatible package

MAXIMUM RATINGS

I_L	250 mA
V_{CEO}	40 V
P_{DISS}	250 mW @ $T_C = 25^\circ C$
T_J	-40 to +100 $^\circ C$
T_{ST}	-40 to +100 $^\circ C$

PACKAGE STYLE TO-92(V1)

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	3.43	4.60	0.135	0.185
B	2.79	3.30	0.110	0.130
C	2.03	3.18	0.080	0.125
D	0.43	0.60	0.017	0.024
F	1.14	1.40	0.045	0.055
G	2.54 BSC		0.100 BSC	
H	1.52 BSC		0.060 BSC	
J	0.23	0.56	0.009	0.022
K	12.83	19.05	0.505	0.750
N	3.05	3.30	0.120	0.130
Q	0.76	1.52	0.030	0.060
R	3.81	4.60	0.150	0.185

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS $T_A = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_D	$I_C = 1 \text{ mA}$	40	60		V
I_L	$V_{CE} = 12 \text{ V}$			100	nA
	$V_{CE} = 5 \text{ V}$ $H = 500 \mu W/cm^2$	5			mA
C_{CE}	$V_{CE} = 10 \text{ V}$ $f = 1 \text{ MHz}$		3.2		pF
$V_{CE(sat)}$	$V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}$ $H = 500 \mu W/cm^2$		0.75	1.0	V
t_{on}	$V_{CE} = 10 \text{ V}$ $R_L = 100 \Omega$ $H = 500 \mu W/cm^2$		125		μS
t_{off}	$V_{CE} = 10 \text{ V}$ $R_L = 100 \Omega$ $H = 500 \mu W/cm^2$		150		μS